## ADVISORY ON THE USE OF THIS DOCUMENT

The information contained in this document has been developed solely for the purpose of providing general guidance to employees of the Goddard Space Flight Center (GSFC). This document may be distributed outside GSFC only as a courtesy to other government agencies and contractors. Any distribution of this document, or application or use of the information contained herein, is expressly conditioned upon, and is subject to, the following understandings and limitations:

- (a) The information was developed for general guidance only and is subject to change at any time;
- (b) The information was developed under unique GSFC laboratory conditions which may differ substantially from outside conditions;
- (c) GSFC does not warrant the accuracy of the information when applied or used under other than unique GSFC laboratory conditions;
- (d) The information should not be construed as a representation of product performance by either GSFC or the manufacturer;
- (e) Neither the United States government nor any person acting on behalf of the United States government assumes any liability resulting from the application or use of the information.

# UNİSYS

٠.

C.S. Eveland

Department

Code 311

From

K. Sahu

Department

7813

Subject

Radiation Report on ISTP Common

Buy Part No. HS2-3530RH-Q.

interoffice Memorandum

PPM-91-003

Date

January 2, 1991

Location

**GSFC** 

Telephone:

731-8661

Location

Lanham

cc

S. Pszcolka/311

V. Edson

S. Esmacher

D. Krus

M. Haines

M. Fowler

A radiation evaluation was performed on HS2-3530RH-Q to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a cobalt 60 gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation steps were 50 and 100 krads. After 100 krads, parts were annealed at 25°C for 24 and 168 hours, and then the irradiation was continued up to 200 and 300 krads (cumulative). The dose rate was between 2.5-5 krads/hour, depending on the total dose level (see Table I for radiation schedule). After each radiation exposure and annealing treatment, parts were electrically tested according to the test conditions and the specification limits listed in Table III.

All parts passed all tests on irradiation up to 50 krads. At 100 krads, two parts marginally exceeded the specification limits on input bias current (Ib+ and Ib-). These two parts were measuring approximately 25 nA, while the specification limit was 20 nA. However, all other parts were well within the specification limits for all tests on irradiation up to 100 krads. On annealing the parts for 24 and 168 hours, the parts showed partial recovery in Ib+ and Ib-.

On continued irradiation to 200 and 300 krads (cumulative), all parts exceeded the specification limits on Tb+, Tb-, and open loop gain (AOL). No significant degradation was observed for any other parameter. Table IV provides a summary of the electrical measurements after total dose exposures and annealing.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at 731-8661.

Physical Inches

#### TABLE I. Part Information

Generic Part Number:

HS2-3530RH-Q

ISTP Common Buy

Part Number:

HS2-3530RH-Q

ISTP Common Buy

Control Number:

436

Manufacturer:

Harris

Quantity Procured:

378

Lot, Date Code:

9010

Quantity Tested:

3.0

Serial Numbers of

Radiation Samples:

23,24,25,26,27,28,29,30

Serial Numbers of Control Samples:

concror samples

21,22

Part Function:

Low Power Programmable Operational

Amplifier

Part Technology:

Bipolar, Radiation Hardened

Package Style:

TO-99 (radial lead - 8 pin)

TABLE II. Radiation Schedule

EVENTS	DOSE RATE	DATE
1) Initial Electrical Measur	cements .	10/15
2) 50 krads irradiation Post 50krads Electrical Meas	2.5 krads/hr surements	10/15 10/16
3) 100 krads irradiation Post 100krads Electrical Mea		10/16 10/17
4) 24 hrs annealing Post 24 hr Electrical Measur	rements	<i>;</i> 10/18
5) 168 hrs annealing Post 168 hr Electrical Meast	rements.	10/24
6) 200 krads irradiation Post 200krads Electrical Mea		10/24 10/25
7) 300 krads irradiation Post 300krads Electrical Mea		10/25 10/26

All electrical measurements performed at 25°C. All parts radiated under bias, see Figure 1. Annealing performed at 25°C under bias, see Figure 1.

TABLE III. Electrical Characteristics and Test Specifications for HS2-3530RH-Q 1),2).

		BIN#:	L	BI	£#3	
Parameter	Symbol	min	xsm	min	max	Units
Offset Voltage	vos	_	3		3	mV
Input Bias Current	Ibias		20	<del> </del>	·	mV
Input Offset Current	IOS		5			nA
Large Siganl				1		
Voltage Gain	AOL	80		65		kV/V
Common Mode				1		<del></del>
Rejection Ratio	CMRR	80		80		dB
Supply Current	icc		150		15	uA
Power Supply		 		1		
Rejection Ratio	PSRR	80		80		đВ
Output Voltage Swing	vo	±12.5		±12.5		v

		BIN#	2	BI		
Parameter	Symbol	min	max	min	max	Units
Large Signal		:	-	1		
Voltage Gain	AOL	25		2.5		kV/V
Common Mode				<del></del>		
Rejection Ratio	CMRR	80		80		đВ
Supply Current	ICC		150		15	uА
Power Supply				<u> </u>		
Rejection Ratio	PSRR	80		80		dВ
Output Voltage Swing	vo	±2.0		±2.0		v
Offset Voltage	VOS		3		3	Vm

#### Notes:

1) The following nomenclature is used for the test measurements under different conditions:

BIN#1: Vs = ±15V, Iset = 15uA BIN#2: Vs = ±3V, Iset = 15uA BIN#3: Vs = ±15V, Iset = 1.5uA BIN#4: Vs = ±3V, Iset = 1.5uA

<sup>&</sup>quot;' VO measurements at Vs = ±3V could not be made reliably because of fficulty with test equipment. These measurements are therefore not included in Table IV.

BIN#1, VS = ±15V ,ISET = 15uA	BIN#1.	VS :	* ±15V	.ISET		15uA
-------------------------------	--------	------	--------	-------	--	------

							Total Dose Exposure (krads)												
				Initi	als	50		100		Annealing 24 hrs.		at 25		200		30	00		
Paramet	ters	Spec.	Limits max	mean	sđ	mean	вd	mean	sd	mean	sđ.	жеар	s d	mean	ьa	   mean	sd		
icc	UA		150	142.5	4.8	129,5	5.1	129.9	5.3	129.3	5.4	128.8	3.2	125	5.B	125.3	4.9		
-100	uA	-150		-126	7.6	-116	8.8	-114	5.2	-115	6.7	-114	6.5	-113	5	-109	6.5		
V0S1	мV		3.0	0.3	1.2	0.3	1.1	0.4	1.1	0.4	1.1	0.4	1.1	0.5	1.1	0.6	1.1		
ios	nA	<u> </u>	5.0	-0.3	0.5	-0.5	0.9	-0.7	1.2	-0.6	1.2	-0.5	1	+0.8	1.5	-1	1.8		
Ib•	nА		20	9.8	1.7	13.6	2.8	19.2	3.6	18.2	3.4	17.2	3.1	32.1	6.5	39.3	7.6		
Ib-	nA		20	10.1	1.9	14.2	2.6	19.9	3.6	18,8	3.6	17.7	3.4	33	6.4	40.1	7.7		
Ibias	κα		20	9.9	1.8	13.9	2.6	19.6	3.6	18.4	3.4	17.4	3.2	32.6	6.4	39.6	7.5		
vos2	mΥ		3.0	0.3	1.2	0.3	1.1	0.2	1.1	0.4	1.1	0.4	1.1	0.5	1.1	0.6	1.1		
AOL	kV/V	80		141.6	9	110.3	6.7	94.4	6.6	97.6	7.1	101.5	7.3	75.5	6.7	54.1	6.1		
CMRR	dB	80		96.1	3	94.4	2.4	93	2.1	93.4	2.4	93.4	2,4	91.3	2	90.1	1.8		
• PSRR	dB.	80		112.4	10.7	106.1	3.9	104.3	3.6	104.3	3.1	104.6	3.7	101.6	2.7	99.8	2.2		
-PSRR	ďВ	80		105.5	5,4	105.5	5.4	105.3	1.9	105.6	5.4	105.8	5.6	106.1	5.7	105.5	5.3		
+۷0	<u>v</u>	12.5		14.1	0	14.1	0	14.1	0	14.1	0	14.1	Đ	14.1	0	14.1	0		
-və		12.5		-13.1	0.1	-13.1	0	-13.1	0	-13.1	0	-13.1	0	-13	0	-13	a		

### BIN#2, VS = $\pm 3V$ , ISET = 15uA

		Spec.	Limita	Initia	115	:	50	10	0	24	hrs.	158	hrs.	20	0	30	10
Paramet	ers	min	max	mean	<b>s</b> d	mean	5d	mean	sd	mean	sd	mean	8d	mean	Бđ	mean	вd
ice	υĄ		150	124.1	5.6	114.5	5.4	110,6	5.8	113.8	4.7	113.8	3.5	110.9	6.4	110.5	5.6
-ICC	uλ	~150		-108	5.1	-97	4.5	-98	5.6	-99	5.9	-97.3	6.4	-96.8	4.9	-95.3	5
VOS1	mΥ		3.0	0.3	1.1	0.2	1.1	0.3	1.1	0.3	1.1	0.2	1.1	0.4	1.1	0.4	1.1
AOL	kV/V	25		77.1	5.8	56.6	3,5	49.1	3.8	50.9	2.7	50.1	2.6	38,6	2.5	32.9	3.2
CMRR	dВ	80		95.1	4.8	93.3	3,4	90.9	2.4	91.1	2.5	91:5	2.7	88.3	2	87.5	4.3
• PSRR	dВ	80		102.1	. 4	98	2.4	95.8	2.2	96.9	2	96.6	1.9	94.6	1.9	93.4	1.4
-PSRR	dВ	80		110.3	4.8	107.9	5.4	108.0	4.7	107.1	3.7	107.6	4	106.9	4.7	106.3	3.6

 $BIN#3. VS = \pm 15V. ISET = 1.5uA$ 

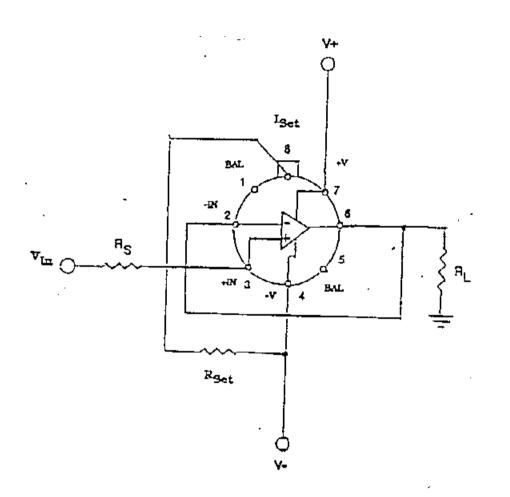
							2 1 1 1 1 L	, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		1001		un					
						Total Dose Exposure (krads)											
				Initi	als	50		100		Ann	Annealing at 25°C			2	00	300	
										24 h	TB.	168	hrs.				
		Spec.	Limits			1								1			
Paramete	èrs .	min	лах	mean	ad	mean	sd_	mean	ьa	mean	sđ	mean	sd	mean	s d.	mean	s d
ICC	u	İ	15	12.7	2.2	12.6	1.5	13.3	3.4	10.7	1.7	12.4	1.0	10.8	3.3	11.7	1.9
-ICC(-)	ųλ		15	11.9	1.7	10.8	2,2	12.1	2.3	11.2	3.6	11.1	2.1	8.8	3.2	9.3	2.9
VOSI	mV	1	3	0.1	1.1	0.4	1.0	0.4	1.0	0.5	1.0	0.4	1.0	0.8	0.9	0.9	1.3
IOS	pA	Ī	5000	8.2	67	-32	128	-67	215	-52	205	-40	171	-125	315	-99	520
VOS2	μV		3000	0.1	1.1	0,4	1.0	0.4	1.0	0.5	1.0	0.4	1.0	0.8	0.9	0.8	1.3
AOL	kv/v	65		128	9	92	7	74	7	77	7	80	6	49	7	33	12
CMRR	đВ	80		95	3	93	2	91	2	91	2	91	2	89	2	97	2
*PSRR	đВ	80		109	5	104	4	103	4	103	4	103	3	100	3	96	3
-25 <b>RR</b>	đВ	80		104	5	103	5	105	4	104	5	102	4	104	5	105	4
+Ÿ0	V	12.5		14.2	0	14.2	0	14.2	0	14.2	a	14.2	0	14.2	0	14.2	0
-vo(-)	v	12.5		13.3	0	13.2	0	13.2	0	13,2	0	13.2	0	13.2	0	12.8	0.3

BIN#4, VS =  $\pm 3V$ , ISET = 1.5uA

			Spec. Limits		Initials		50		100		24 hrs		158 hrs.		200		o a
Paramete	ers	min	MΦX	mean	sd	mean	ьd	mean	Бa	mean	ьa	mean	sđ	mean	ad	mean	ಕಡೆ
ICC	uА		15	10.6	3.7	11.4	1.8	11.2	2.2	10.9	1.9	9.0	1.9	10.3	1.8	10.0	2.0
-ICC(-)	uλ	1.	15	8,4	3.1	7.2	7.5	10.3	1.9	8.0	2.4	7.8	1.8	9.6	2.3	7.5	2.9
VOSI	ŊΨ		3.0	0.3	1.0	0.3	1.0	0.4	0.9	0.4	1.0	0.3	1.0	0.6	0,9	9.2	23
AOL	kv/v	25		64	4	47	5	35	3	39	3	40	4	25	4	20	3
CMRR	фB	80	i	91	3	89	2	87	2	87	2	87	2	84	1	82	2
+PSRR	đВ	80		100	3	97	2	9.5	2	96	3	95	2	92	2	91	3
-PSRR	₫B	80		109	6	111	5	111	8	109	9	113	9	109	7	105	4

#### Notes:

- 1/ The mean and standard deviation values were calculated over the eight parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.
- 2/ Vo measurements at Vs =  $\pm 3V$  could not be made reliably because of difficulty with test equipment; therefore these measurements are not included in Table IV.



## Notes:

Rs shall be 820 Ohm, 0.25 watt  $\pm 5$ % RL shall be 3.3 kOhm, 0.25 watt  $\pm 5$ % RSET shall be 1 MOhm, 0.25 watt  $\pm 5$ %

FIGURE 1. Radiation Bias Circuit